

# C1210C332JCGACTU

Aliases (C1210C332JCGAC7800) SMD Comm COG HV, Ceramic, 3,300 pF, 5%, 500 VDC, COG, SMD, MLCC, Ultra-Stable, Low Loss, Class I, 1210, 1.5 mm



General Information				
Series	SMD Comm COG HV			
Style	SMD Chip			
Description	SMD, MLCC, Ultra-Stable, Low Loss, Class I			
Features	Ultra-Stable, Low Loss, Class I			
RoHS	Yes			
Termination	Tin			
Marking	No			
AEC-Q200	No			
Typical Component Weight	95 mg			
Shelf Life	78 Weeks			
MSL	1			

3,300 pF

100 GOhms

Dimensions	
Chip Size	1210
L	3.2mm +/-0.2mm
W	2.5mm +/-0.2mm
Т	2.5mm +/-0.30mm
S	1.5mm MIN
В	0.5mm +/-0.25mm

	3.2mm +/-0.2mm	Measurement Condition	1 kHz 1.0Vrms
	2.5mm +/-0.2mm	Tolerance	5%
	2.5mm +/-0.30mm	Voltage DC	500 VDC
	1.5mm MIN	Dielectric Withstanding Voltage	750 VDC
	0.5mm +/-0.25mm	Temperature Range	-55/+125°C
		Temp. Coefficient	COG
ons	T&R, 180mm, Plastic Tape	Capacitance Change with Reference to +25°C and 0 VDC Applied (TCC)	30 ppm/C, 1kHz 1.0Vrms
1000	Dissipation Factor	0.1% 1 kHz 1.0Vrms	
		Aging Rate	0% Loss/Decade Hour

Insulation Resistance

**Specifications** 

Capacitance

S	1.5mm MIN	Dielectric Withstanding Voltage	750 VDC
B 0.5mm +/-0.25mm		Temperature Range	-55/+125°C
		Temp. Coefficient	COG
Packaging Specifications		Capacitance Change with	30 ppm/C, 1kHz 1.0
Packaging	T&R, 180mm, Plastic Tape	Reference to +25°C and 0 VDC Applied (TCC)	
Packaging Quantity	1000	Dissipation Factor	0.1% 1 kHz 1.0Vrms
		Dissipation ractor	0.170 TRI 12 1.0 VIIII3

Statements of suitability for certain applications are based on our knowledge of typical operating conditions for such applications, but are not intended to constitute - and we specifically disclaim - any warranty concerning suitability for a specific customer application or use. This Information is intended for use only by customers who have the requisite experience and capability to determine the correct products for their application. Any technical advice inferred from this Information or otherwise provided by us with reference to the use of our products is given gratis, and we assume no obligation or liability for the advice given or results obtained.

Generated 04/30/2025 © 2006 - 2025 YAGEO

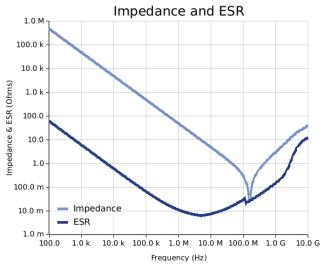


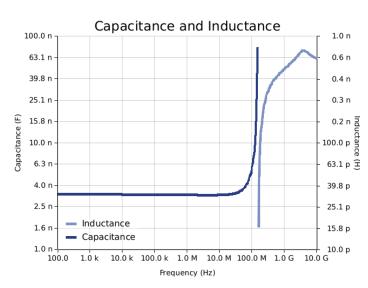
# C1210C332JCGACTU

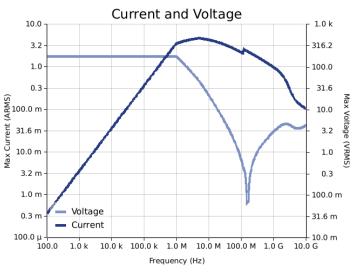
Aliases (C1210C332JCGAC7800) SMD Comm COG HV, Ceramic, 3,300 pF, 5%, 500 VDC, COG, SMD, MLCC, Ultra-Stable, Low Loss, Class I, 1210, 1.5 mm

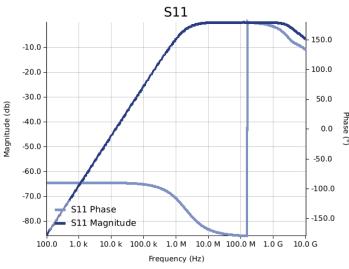
### **Simulations**

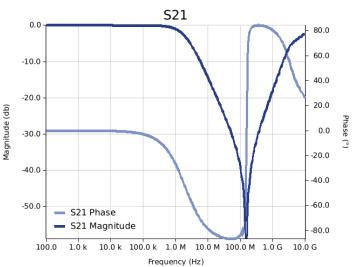
For the complete simulation environment please visit K-SIM.











Generated 04/30/2025 © 2006 - 2025 YAGEO



### C1210C332JCGACTU

Aliases (C1210C332JCGAC7800) SMD Comm COG HV, Ceramic, 3,300 pF, 5%, 500 VDC, COG, SMD, MLCC, Ultra-Stable, Low Loss, Class I, 1210, 1.5 mm

#### These are simulations.

This is not a specification!

The responses shown represent the typical response for each part type. Specific responses may vary, depending on manufacturing variation affects of all parameters involved, including the specified tolerances applied to capacitance and unspecified variations of ESR, ESL, and leakage resistance.

The responses shown do not represent a specified or implied maximum capability of the device for all applications.

- The ESR used for ripple "Ripple Current/Voltage vs. Frequency" plots is the ESR at ambient temperature.

- The ESR used for ripple Ripple Currenty votage vs. rrequency plots is unleast at an interact temperature.
  The ESR in the "Temperature Rise vs. Ripple Current" plots is adjusted to each incremental temperature rise before the power and ripple current is calculated.
  The effects shown herein are based on measured data from a multiple part sample of the parts in question.
  Ripple capability of this device will be factored by thermal resistance (Rth) created by circuit traces (addi affects of all parameters involved, including the specified tolerances applied to capacitance and unspecified variations of ESR, ESL, and leakage resistance.
  The peak voltages generated in the "Temperature Rise vs. Combined Ripple Currents" plot are calculated for each frequency and are not combined with voltages
- generated at any other harmonics.

   Please consult with the catalog or field applications engineer for maximum capability of the device in specific applications.

All product information and data (collectively, the "Information") are subject to change without notice.

KEMET K-SIM is designed to simulate behavior of components with respect to frequency, ambient temperature, and DC bias levels. The responses shown represent the typical response for each part type. Specific responses may vary, depending on manufacturing variation effects of all parameters involved, including the specified tolerances applied to capacitance and unspecified variations of ESR, ESL, and leakage resistance.

All Information given herein is believed to be accurate and reliable, but is presented without guarantee, warranty, or responsibility of any kind, expressed or implied. Statements of suitability for certain applications are based on our knowledge of typical operating conditions for such applications, but are not intended to constitute – and we specifically disclaim – any warranty concerning suitability for a specific customer application or use. This Information is intended for use only by customers who have the requisite experience and capability to determine the correct products for their application. Any technical advice inferred from this Information or otherwise provided by us with reference to the use of our products is given gratis, and we assume no obligation or liability for the advice given or results obtained.

If you have any questions please contact K-SIM.

Generated 04/30/2025 © 2006 - 2025 YAGEO